

Contents

Part I. Basic Concepts

| | |
|---|----|
| 1. Introduction | 3 |
| 1.1 Epitaxial Crystallization Process | 3 |
| 1.2 Growth Modes in Epitaxy | 6 |
| 2. Homo- and Heteroepitaxial Crystallization Phenomena ... | 11 |
| 2.1 Nucleation and Epitaxy | 11 |
| 2.2 Defects in Epitaxial Layers | 15 |
| 2.2.1 Point Defects | 16 |
| 2.2.2 Dislocations | 16 |
| 2.2.3 Stacking Faults | 18 |
| 2.2.4 Twins | 19 |
| 2.2.5 Antiphase Domain Boundaries | 21 |
| 2.2.6 "Superdislocations" | 22 |
| 2.2.7 Misfit Dislocations | 23 |
| 2.3 Peculiarities of Epitaxially Grown Layers | 25 |
| 2.3.1 Homoepitaxial Layers | 25 |
| 2.3.2 Heteroepitaxial Layers | 28 |
| 3. Application Areas of Epitaxially Grown Layer Structures . | 35 |
| 3.1 Low-Dimensional Heterostructures | 35 |
| 3.2 Device Structures with Epitaxial Layers | 37 |

Part II. Technical Implementation

| | |
|--|----|
| 4. Solid Phase Epitaxy | 45 |
| 4.1 Technological Procedures | 46 |
| 4.1.1 Formation of the Amorphous Phase | 48 |
| 4.1.2 Programmed Heating of the a/c System | 51 |
| 4.2 Measurement of the Growth Rate | 52 |
| 4.3 Application Areas | 54 |
| 4.3.1 Growth of Highly Doped Epilayers | 54 |
| 4.3.2 Growth of Buffer Layers | 58 |

| | |
|--|-----|
| 5. Liquid Phase Epitaxy | 63 |
| 5.1 Standard Techniques | 64 |
| 5.1.1 Transport Processes | 66 |
| 5.1.2 Two-Dimensional Effects | 68 |
| 5.1.3 LPE of Compound Semiconductors | 69 |
| 5.2 Liquid Phase Electroepitaxy | 73 |
| 5.3 The LPEE Process and Related Phenomena | 74 |
| 5.3.1 Growth Kinetics in LPEE of GaAs | 76 |
| 5.3.2 The Peltier Effect at the GaAs-substrate/(Ga-As)-Solution Interface.... | 77 |
| 6. Vapor Phase Epitaxy | 81 |
| 6.1 Physical Vapor Deposition | 84 |
| 6.1.1 Evaporation Rates | 84 |
| 6.1.2 Langmuir and Knudsen Modes of Evaporation | 85 |
| 6.1.3 Principles of MBE | 87 |
| 6.1.4 Sputtering | 88 |
| 6.1.5 Film Deposition in a Glow Discharge | 89 |
| 6.1.6 Sputtering and Epitaxy | 93 |
| 6.1.7 Pulsed Laser Deposition | 97 |
| 6.2 Chemical Vapor Deposition | 102 |
| 6.2.1 Principles of CVD Processes | 102 |
| 6.2.2 Mass Transport and Heat Transfer in CVD Reactors .. | 109 |
| 6.2.3 Principles of the MOVPE Process | 120 |
| 6.3 Atomic Layer Epitaxy | 121 |
| 6.3.1 Principles of the ALE Process | 121 |
| 6.3.2 Growth Systems for CVD-like ALE | 126 |
| 6.3.3 Specific Features and Application Areas | 127 |
| 7. Molecular Beam Epitaxy | 131 |
| 7.1 Solid Source MBE | 133 |
| 7.1.1 Basic Phenomena | 135 |
| 7.1.2 Evaporation Sources | 140 |
| 7.2 Gas Source MBE | 146 |
| 7.2.1 Beam Sources Used in GSMBE | 147 |
| 7.2.2 Metal Organic MBE | 150 |
| 7.2.3 Hydride Source MBE | 152 |
| 7.3 Growth Techniques Using Modulated Beams | 155 |
| 7.3.1 Ultrahigh Vacuum Atomic Layer Epitaxy | 156 |
| 7.3.2 Migration Enhanced Epitaxy | 159 |
| 7.3.3 Molecular Layer Epitaxy | 161 |
| 7.4 Externally Assisted MBE | 164 |
| 7.4.1 Irradiation with UV Light in MLE of GaAs | 164 |
| 7.4.2 Ion-Assisted Doping in Si-MBE | 165 |

| | | |
|-----------|--|------------|
| 7.4.3 | Plasma-Assisted MBE Growth of GaN and Related Compounds | 169 |
| 8. | Metal Organic Vapor Phase Epitaxy | 171 |
| 8.1 | Basic Concepts | 171 |
| 8.2 | Growth Equipment | 176 |
| 8.2.1 | Commercial MOVPE Reactors | 176 |
| 8.2.2 | Gas-Vapor Delivery Systems in MOVPE | 181 |
| 8.3 | Precursor Materials | 185 |
| 8.4 | Precursor Decomposition and Reactions | 190 |
| 8.5 | Control of Surfaces Before and During Growth | 194 |
| 8.6 | Nonthermal MOVPE Techniques | 196 |
| 8.6.1 | Photo-MOVPE | 197 |
| 8.6.2 | Plasma-MOVPE | 198 |
| 8.7 | Safety Aspects of MOVPE | 198 |

Part III. In-situ Analysis of the Growth Processes

| | | |
|------------|---|------------|
| 9. | In-situ Analysis of Species and Transport | 203 |
| 9.1 | Identification of the Growth Relevant Species | 203 |
| 9.1.1 | Mass Spectrometry | 204 |
| 9.1.2 | Optical Identification of Species | 208 |
| 9.2 | Mass Transport to the Surface | 216 |
| 9.2.1 | Measurement of Velocities | 217 |
| 9.2.2 | Measurement of Temperature | 220 |
| 10. | In-situ Surface Analysis | 225 |
| 10.1 | Scanning Microscopes | 226 |
| 10.2 | Diffractions Techniques | 228 |
| 10.2.1 | Diffraction | 229 |
| 10.2.2 | RHEED | 231 |
| 10.2.3 | GIXS | 232 |
| 10.3 | Reflectance Based Optical Techniques | 234 |
| 10.3.1 | Reflectance of Polarized Light | 236 |
| 10.3.2 | Reflectance Anisotropy Spectroscopy (RAS) | 240 |
| 10.3.3 | Ellipsometry | 247 |
| 10.3.4 | P-polarized Reflectance Spectroscopy (PRS) Surface Photoabsorption (SPA) | 253 |
| 10.3.5 | Reflectometry | 255 |
| 10.4 | Other Optical Techniques | 256 |
| 10.4.1 | Laser Light Scattering (LLS) | 256 |
| 10.4.2 | Second Harmonic Generation (SHG) | 258 |
| 10.4.3 | Raman Spectroscopy | 259 |
| 10.4.4 | Infrared Reflection Absorption Spectroscopy (IRRAS) | 263 |

Part IV. Physics of Epitaxy

| | |
|--|-----|
| 11. Thermodynamic Aspects | 267 |
| 11.1 The Driving Force for Epitaxy | 268 |
| 11.1.1 Basic Concepts and Terminology of Thermodynamics . | 268 |
| 11.1.2 The Interphase Exchange Processes | 270 |
| 11.2 Mass Transport Phenomena | 271 |
| 11.2.1 Basic Equations Describing Mass Transport in VPE Systems | 271 |
| 11.2.2 The Boundary Layer at the Substrate Surface | 273 |
| 11.2.3 Effusion from Solid Sources in MBE | 276 |
| 11.3 Phase Equilibria and Phase Transitions | 284 |
| 11.3.1 Ideal and Regular Solutions | 284 |
| 11.3.2 The Liquid–Solid Phase Diagram | 288 |
| 11.3.3 Phase Transitions in Epitaxy | 292 |
| 11.4 Interface Formation in Epitaxy | 296 |
| 11.4.1 The Interface Energy | 296 |
| 11.4.2 Initial Stages of Epitaxial Growth | 299 |
| 11.5 Self-Organization Processes | 302 |
| 11.5.1 Strain-Induced Self-Ordering; Quantum Dots | 304 |
| 11.5.2 Strain-Induced Lateral Ordering; Quantum Wires . . . | 311 |
| 11.6 Morphological Stability in Epitaxy | 316 |
| 11.6.1 The Mullins–Sekerka Theory | 316 |
| 11.6.2 Morphological Stability in LPE | 318 |
| 12. Atomistic Aspects | 321 |
| 12.1 Incorporating of Adatoms into a Crystal Lattice | 321 |
| 12.1.1 Kossel’s Model of Crystallization | 321 |
| 12.1.2 Lattice Gas Models | 324 |
| 12.1.3 Stochastic Model of Epitaxy | 327 |
| 12.2 Adsorption–Desorption Kinetics | 332 |
| 12.2.1 Adsorption Isotherms; Phenomenological Treatment . | 332 |
| 12.2.2 Adsorption Isotherms; Statistical Treatment | 334 |
| 12.2.3 Thermal Desorption Kinetics | 337 |
| 12.3 Step Advancement and Bunching Processes | 344 |
| 12.3.1 Growth Conditions on Vicinal Surfaces | 344 |
| 12.3.2 Step Advancement Kinetics | 345 |
| 12.3.3 Mass Transport Between Steps; Step Bunching | 348 |
| 13. Quantum Mechanical Aspects | 351 |
| 13.1 Framework of Quantum Mechanics | 351 |
| 13.1.1 Interatomic Bonds in Small Molecules | 355 |
| 13.1.2 Chemical Bonds in Solid Crystals | 358 |
| 13.1.3 Bonding at Surfaces | 360 |

| | |
|--|-----|
| 13.2 Surface Structure | 365 |
| 13.2.1 Physical Principles | 365 |
| 13.2.2 Reconstructed Surfaces; Theoretical Methodology | 368 |
| 13.2.3 Reconstructed Surfaces; Materials-Related Examples .. | 372 |
| 13.3 Substrate Surface Structure and the Epitaxial Growth Processes | 378 |
| 13.3.1 GaAs(001) Homoepitaxy | 378 |
| 13.3.2 Quantum Dots Grown on Surfaces of Different Reconstruction | 380 |
| 13.3.3 Ordering in InGaP | 385 |
| <hr/> | |
| Part V. Heteroepitaxy | |
| <hr/> | |
| 14. Heteroepitaxy; Growth Phenomena | 389 |
| 14.1 Nearly Lattice-Matched Heterostructures | 389 |
| 14.1.1 Critical Thickness; Theoretical Treatment | 391 |
| 14.1.2 Critical Thickness; Experimental Data | 394 |
| 14.1.3 Epitaxy on Compliant Substrates | 396 |
| 14.1.4 Highly Strained Heterostructures | 401 |
| 14.1.5 Surfactant-Mediated Heteroepitaxy | 402 |
| 14.1.6 Heteroepitaxial Lateral Overgrowth | 405 |
| 14.1.7 Hard Heteroepitaxy | 413 |
| 14.2 Artificial Epitaxy (Graphoepitaxy) | 415 |
| 14.2.1 General Principles of Graphoepitaxy | 416 |
| 14.2.2 Growth Mechanisms in Graphoepitaxy | 418 |
| 15. Material-Related Problems of Heteroepitaxy | 423 |
| 15.1 Material Systems Crystallizing by the Fundamental Growth Modes | 423 |
| 15.1.1 Growth by the Island Mode | 424 |
| 15.1.2 Growth by the Layer-by-Layer Mode | 425 |
| 15.1.3 Growth by the Layer-Plus-Island Mode | 426 |
| 15.2 Peculiarities of Heteroepitaxy of Selected Material Groups ... | 429 |
| 15.2.1 Group III Nitrides | 430 |
| 15.2.2 IV-VI Compound Semiconductors | 438 |
| 15.2.3 Organic Semiconductors | 452 |
| 16. Closing Remarks | 465 |
| References | 467 |
| List of Abbreviations | 500 |
| List of Metalorganic Precursors | 505 |
| Index | 507 |